Product data sheet

1. General description

The 74LVC10A provides three 3-input NAND functions.

Inputs can be driven from either 3.3 V or 5 V devices. This feature allows the use of these devices as translators in mixed 3.3 V and 5 V applications.

2. Features and benefits

- Wide supply voltage range from 1.2 V to 3.6 V
- Inputs accept voltages up to 5.5 V
- CMOS low power consumption
- Direct interface with TTL levels
- Latch-up performance exceeds 250 mA
- Complies with JEDEC standard:
 - ◆ JESD8-7A (1.65 V to 1.95 V)
 - ◆ JESD8-5A (2.3 V to 2.7 V)
 - JESD8-C/JESD36 (2.7 V to 3.6 V)
- ESD protection:
 - ◆ HBM JESD22-A114F exceeds 2000 V
 - MM JESD22-A115-B exceeds 200 V
 - CDM JESD22-C101E exceeds 1000 V
- Specified from -40 °C to +85 °C and -40 °C to +125 °C

3. Ordering information

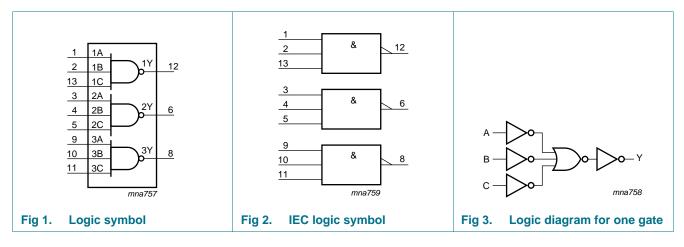
Table 1.Ordering information

Type number	Package						
	Temperature range Name		Description	Version			
74LVC10AD	–40 °C to +125 °C	SO14	plastic small outline package; 14 leads; body width 3.9 mm	SOT108-1			
74LVC10ADB	–40 °C to +125 °C	SSOP14	plastic shrink small outline package; 14 leads; body width 5.3 mm	SOT337-1			
74LVC10APW	–40 °C to +125 °C	TSSOP14	plastic thin shrink small outline package; 14 leads; body width 4.4 mm	SOT402-1			
74LVC10ABQ	–40 °C to +125 °C	DHVQFN14	plastic dual in-line compatible thermal enhanced very thin quad flat package; no leads; 14 terminals; body $2.5 \times 3 \times 0.85$ mm	SOT762-1			



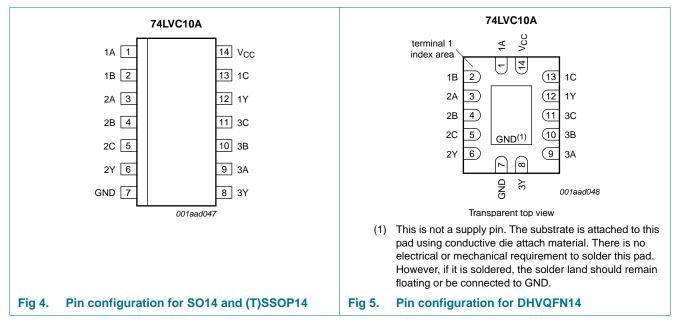
Triple 3-input NAND gate

Functional diagram 4.



5. **Pinning information**

5.1 Pinning



5.2 Pin description

Table 2. Pin description				
Symbol	Pin	Description		
1A, 2A, 3A	1, 3, 9	data input		
1B, 2B, 3B	2, 4, 10	data input		
1C, 2C, 3C	13, 5, 11	data input		

NXP Semiconductors

Table 2. P	in descriptioncontinued	
Symbol	Pin	Description
1Y, 2Y, 3Y	12, 6, 8	data outputs
GND	7	ground (0 V)
V _{CC}	14	supply voltage

6. Functional description

Table 3.	Function selection ^[1]		
Input			Output
nA	nB	nC	nY
L	x	Х	Н
Х	L	Х	Н
Х	Х	L	Н
Н	Н	Н	L

[1] H = HIGH voltage level; L = LOW voltage level; X = don't care

7. Limiting values

Table 4.Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

SymbolParameterConditionsMinMax V_{CC} supply voltage-0.5+6.5 I_{IK} input clamping current $V_I < 0 V$ -50- V_I input voltage[1] -0.5+6.5 I_{OK} output clamping current $V_O > V_{CC}$ or $V_O < 0 V$ -±50 V_O output voltage[2] -0.5 $V_{CC} + 0$ I_O output current $V_O = 0 V$ to V_{CC} -±50	
I_{IK} input clamping current $V_I < 0 V$ -50 -50 V_I input voltage [1] -0.5 $+6.5$ I_{OK} output clamping current $V_O > V_{CC}$ or $V_O < 0 V$ $ \pm 50$ V_O output voltage [2] -0.5 $V_{CC} + 0$	Unit
V_1 input voltage[1] -0.5+6.5 I_{OK} output clamping current $V_O > V_{CC}$ or $V_O < 0$ -±50 V_O output voltage[2] -0.5 $V_{CC} + 0$	V
I_{OK} output clamping current $V_O > V_{CC}$ or $V_O < 0$ V- ± 50 V_O output voltage $\boxed{2}$ -0.5 $V_{CC} + 0$	mA
V_{O} output voltage $(2) -0.5 V_{CC} + 0$	V
	mA
Le output current $V_0 = 0 V t_0 V_{00}$ - +50	.5 V
	mA
I _{CC} supply current - 100	mA
I _{GND} ground current -100 -	mA
P_{tot} total power dissipation $T_{amb} = -40 \ ^{\circ}C$ to $+125 \ ^{\circ}C$ $\boxed{3}$ 500	mW
T _{stg} storage temperature -65 +150	°C

[1] The minimum input voltage ratings may be exceeded if the input current ratings are observed.

[2] The output voltage ratings may be exceeded if the output current ratings are observed.

[3] For SO14 packages: above 70 °C the value of P_D derates linearly with 8 mW/K. For (T)SSOP14 packages: above 60 °C the value of P_D derates linearly with 5.5 mW/K. For DHVQFN14 packages: above 60 °C the value of P_D derates linearly with 4.5 mW/K.

Triple 3-input NAND gate

8. Recommended operating conditions

Table 5.	Recommended operating conditions					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V _{CC}	supply voltage		1.65	-	3.6	V
		functional	1.2	-	-	V
VI	input voltage		0	-	5.5	V
T _{amb}	ambient temperature	in free air	-40	-	+125	°C
$\Delta t/\Delta V$	input transition rise and fall	V_{CC} = 1.65 V to 2.7 V	0	-	20	ns/V
	rate	V_{CC} = 2.7 V to 3.6 V	0	-	10	ns/V

9. Static characteristics

Table 6. Static characteristics

At recommended operating conditions. Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	-40	–40 °C to +85 °C			–40 °C to +125 °C		
			Min	Typ <mark>[1]</mark>	Max	Min	Max		
V _{IH} HIGH-level	V _{CC} = 1.2 V	1.08	-	-	1.08	-	V		
	input voltage	V_{CC} = 1.65 V to 1.95 V	$0.65 \times V_{\text{CC}}$	-	-	$0.65 \times V_{CC}$	-	V	
		V_{CC} = 2.3 V to 2.7 V	1.7	-	-	1.7	-	V	
		V_{CC} = 2.7 V to 3.6 V	2.0	-	-	2.0	-	V	
V _{IL}	LOW-level	V _{CC} = 1.2 V	-	-	0.12	-	0.12	V	
	input voltage	V_{CC} = 1.65 V to 1.95 V	-	-	$0.35 \times V_{CC}$	-	$0.35 \times V_{CC}$	V	
		V_{CC} = 2.3 V to 2.7 V	-	-	0.7	-	0.7	V	
		V_{CC} = 2.7 V to 3.6 V	-	-	0.8	-	0.8	V	
V _{OH}	HIGH-level	$V_{I} = V_{IH} \text{ or } V_{IL}$							
	output voltage	$I_{O} = -100 \ \mu A;$ $V_{CC} = 1.65 \ V \text{ to } 3.6 \ V$	$V_{CC}-0.2$	-	-	$V_{CC}-0.3$	-	V	
		$I_{O} = -4 \text{ mA}; V_{CC} = 1.65 \text{ V}$	1.2	-	-	1.05	-	V	
		I_{O} = -8 mA; V_{CC} = 2.3 V	1.8	-	-	1.65	-	V	
		$I_{O} = -12 \text{ mA}; V_{CC} = 2.7 \text{ V}$	2.2	-	-	2.05	-	V	
		$I_{O} = -18 \text{ mA}; V_{CC} = 3.0 \text{ V}$	2.4	-	-	2.25	-	V	
		$I_{O} = -24$ mA; $V_{CC} = 3.0$ V	2.2	-	-	2.0	-	V	
V _{OL}	LOW-level output voltage	$V_{I} = V_{IH} \text{ or } V_{IL}$							
		$I_{O} = 100 \ \mu A;$ $V_{CC} = 1.65 \ V \text{ to } 3.6 \ V$	-	-	0.2	-	0.3	V	
		I _O = 4 mA; V _{CC} = 1.65 V	-	-	0.45	-	0.65	V	
		I_{O} = 8 mA; V_{CC} = 2.3 V	-	-	0.6	-	0.8	V	
		I_0 = 12 mA; V_{CC} = 2.7 V	-	-	0.4	-	0.6	V	
		$I_0 = 24 \text{ mA}; V_{CC} = 3.0 \text{ V}$	-	-	0.55	-	0.8	V	
lı	input leakage current	V_{CC} = 3.6 V; V_{I} = 5.5 V or GND	-	±0.1	±5	-	±20	μΑ	

4 of 14

Triple 3-input NAND gate

Symbol P	Parameter	neter Conditions	–40 °C to +85 °C			–40 °C to	–40 °C to +125 °C		
			Min	Typ[1]	Max	Min	Max		
I _{CC}	supply current	$\label{eq:VCC} \begin{array}{l} V_{CC} = 3.6 \ V; \ V_{I} = V_{CC} \ \text{or GND}; \\ I_{O} = 0 \ A \end{array}$	-	0.1	10	-	40	μA	
∆I _{CC}	additional supply current	per input pin; V _{CC} = 2.7 V to 3.6 V; V _I = V _{CC} - 0.6 V; I _O = 0 A	-	5	500	-	5000	μΑ	
CI	input capacitance	$V_{CC} = 0 V \text{ to } 3.6 V;$ $V_I = GND \text{ to } V_{CC}$	-	4.0	-	-	-	pF	

Table 6. Static characteristics ...continued

At recommended operating conditions. Voltages are referenced to GND (ground = 0 V).

[1] All typical values are measured at V_{CC} = 3.3 V (unless stated otherwise) and T_{amb} = 25 °C.

10. Dynamic characteristics

Table 7. Dynamic characteristics

Voltages are referenced to GND (ground = 0 V). For test circuit see Figure 7.

Symbol	Parameter	Conditions		–40 °C to +85 °C		–40 °C to +125 °C		Unit	
				Min	Typ[1]	Max	Min	Max	
t _{pd}	propagation delay	nA, nB, nC to nY; see Figure 6	[2]						
		V _{CC} = 1.2 V		-	13	-	-	-	ns
		V_{CC} = 1.65 V to 1.95 V		0.5	4.5	11.2	0.5	12.9	ns
		V_{CC} = 2.3 V to 2.7 V		1.0	2.7	6.3	1.0	7.4	ns
		V _{CC} = 2.7 V		1.5	2.8	6.7	1.5	7.8	ns
		V_{CC} = 3.0 V to 3.6 V		1.5	2.4	5.7	1.5	6.6	ns
C _{PD}	power dissipation	per gate; $V_I = GND$ to V_{CC}	[3]						
	capacitance	V_{CC} = 1.65 V to 1.95 V		-	2.9	-	-	-	pF
		V_{CC} = 2.3 V to 2.7 V		-	6.0	-	-	-	pF
		$V_{CC} = 3.0 \text{ V} \text{ to } 3.6 \text{ V}$		-	8.8	-	-	-	pF

[1] Typical values are measured at T_{amb} = 25 °C and V_{CC} = 1.2 V, 1.8 V, 2.5 V, 2.7 V, and 3.3 V respectively.

[2] t_{pd} is the same as t_{PLH} and t_{PHL} .

[3] C_{PD} is used to determine the dynamic power dissipation (P_D in μ W).

 $P_{D} = C_{PD} \times V_{CC}^{2} \times f_{i} \times N + \Sigma(C_{L} \times V_{CC}^{2} \times f_{o}) \text{ where:}$

 f_i = input frequency in MHz; f_o = output frequency in MHz

 C_L = output load capacitance in pF

 V_{CC} = supply voltage in Volts

N = number of inputs switching

 $\Sigma(C_L \times V_{CC}{}^2 \times f_o)$ = sum of the outputs

Triple 3-input NAND gate

11. AC waveforms

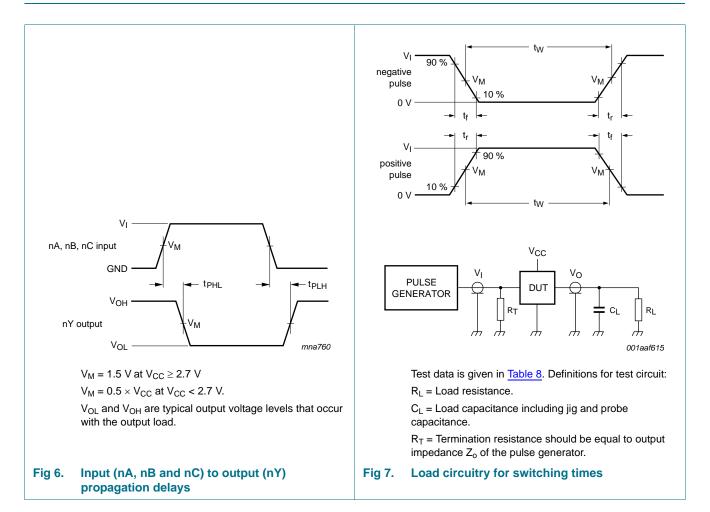


Table 8. Test data

Supply voltage	Input		Load	Load		
	VI	t _r , t _f	CL	RL		
1.2 V	V _{CC}	\leq 2 ns	30 pF	1 kΩ		
1.65 V to 1.95 V	V _{CC}	\leq 2 ns	30 pF	1 kΩ		
2.3 V to 2.7 V	V _{CC}	\leq 2 ns	30 pF	500 Ω		
2.7 V	2.7 V	\leq 2.5 ns	50 pF	500 Ω		
3.0 V to 3.6 V	2.7 V	≤ 2.5 ns	50 pF	500 Ω		

Triple 3-input NAND gate

12. Package outline

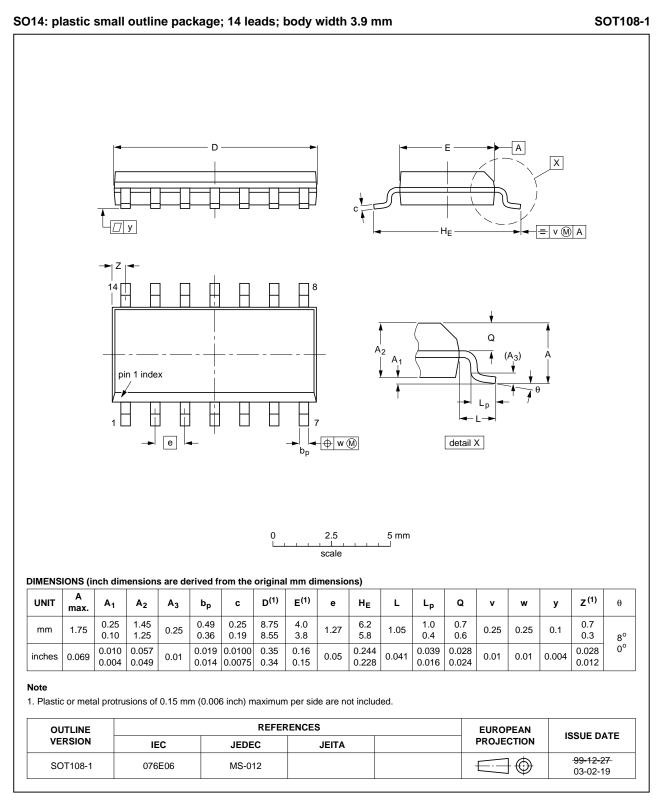


Fig 8. Package outline SOT108-1 (SO14)

All information provided in this document is subject to legal disclaimers.

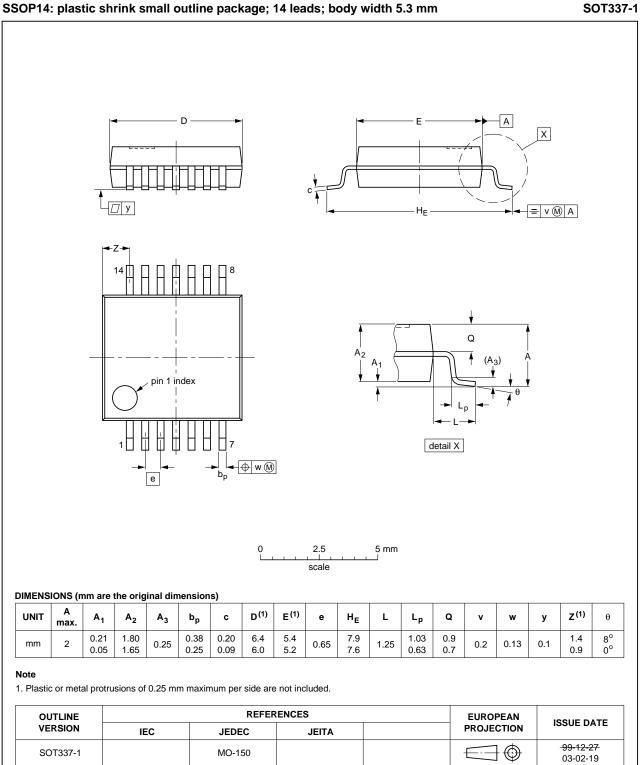


Fig 9. Package outline SOT337-1 (SSOP14)

All information provided in this document is subject to legal disclaimers.

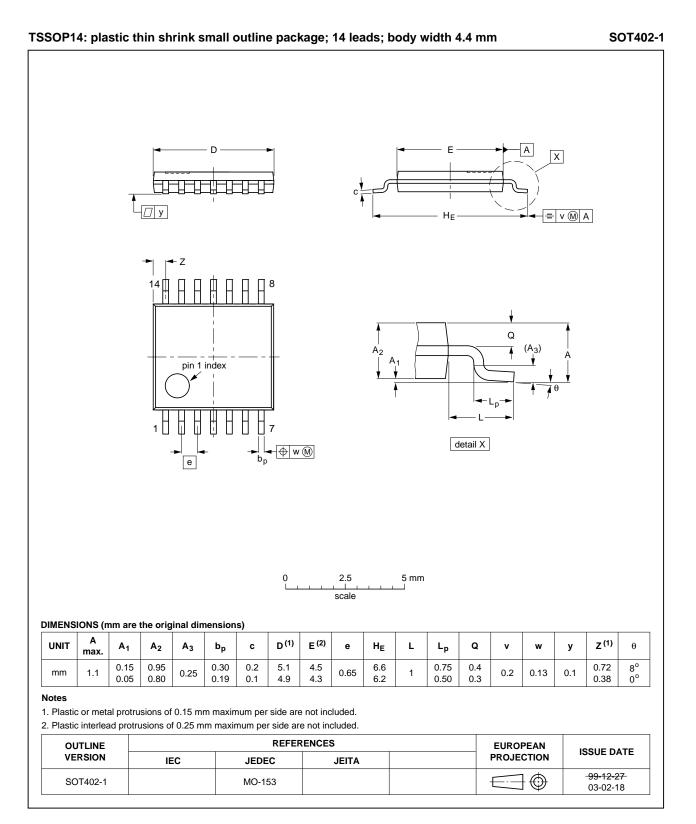
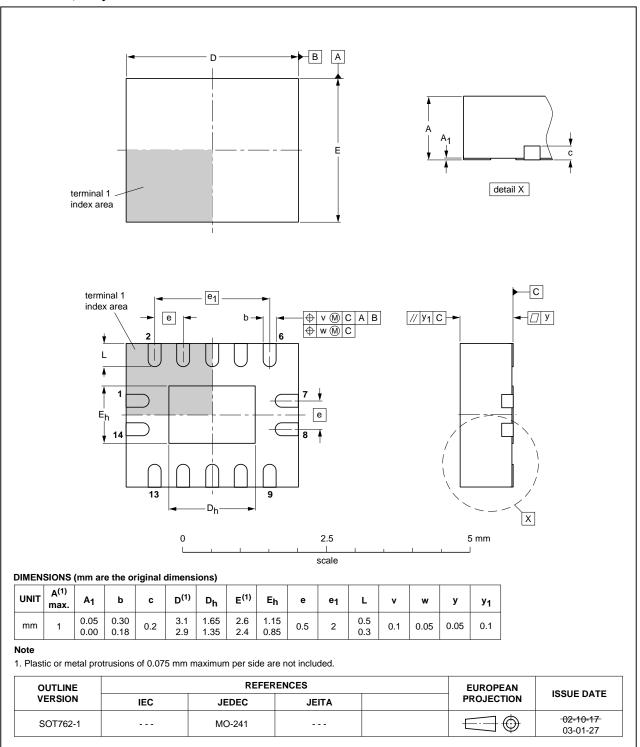


Fig 10. Package outline SOT402-1 (TSSOP14)

All information provided in this document is subject to legal disclaimers.



DHVQFN14: plastic dual in-line compatible thermal enhanced very thin quad flat package; no leads; 14 terminals; body 2.5 x 3 x 0.85 mm SOT762-1

Fig 11. Package outline SOT762-1 (DHVQFN14)

All information provided in this document is subject to legal disclaimers.

74LVC10A



Triple 3-input NAND gate

13. Abbreviations

Table 9.	Abbreviations
Acronym	Description
CDM	Charged Device Model
DUT	Device Under Test
ESD	ElectroStatic Discharge
HBM	Human Body Model
MM	Machine Model
TTL	Transistor-Transistor Logic

14. Revision history

Table 10. R	evision history			
Document II	D Release date	Data sheet status	Change notice	Supersedes
74LVC10A v.	5 20111117	Product data sheet	-	74LVC10A v.4
Modifications	: • Legal pages	s updated.		
	• <u>Table 6</u> , boo	dyrow ΔI_{CC} : condition V_{CC} changed	ged.	
74LVC10A v.	4 20110914	Product data sheet	-	74LVC10A v.3
74LVC10A v.	3 20030620	Product specification	-	74LVC10A v.2
74LVC10A v.	2 19980428	Product specification	-	74LVC10A v.1
74LVC10A v.	1 -	-	-	-

15. Legal information

15.1 Data sheet status

Document status[1][2]	Product status ^[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

[3] The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL http://www.nxp.com.

15.2 Definitions

Draft — The document is a draft version only. The content is still under internal review and subject to formal approval, which may result in modifications or additions. NXP Semiconductors does not give any representations or warranties as to the accuracy or completeness of information included herein and shall have no liability for the consequences of use of such information.

Short data sheet — A short data sheet is an extract from a full data sheet with the same product type number(s) and title. A short data sheet is intended for quick reference only and should not be relied upon to contain detailed and full information. For detailed and full information see the relevant full data sheet, which is available on request via the local NXP Semiconductors sales office. In case of any inconsistency or conflict with the short data sheet, the full data sheet shall prevail.

Product specification — The information and data provided in a Product data sheet shall define the specification of the product as agreed between NXP Semiconductors and its customer, unless NXP Semiconductors and customer have explicitly agreed otherwise in writing. In no event however, shall an agreement be valid in which the NXP Semiconductors product is deemed to offer functions and qualities beyond those described in the Product data sheet.

15.3 Disclaimers

Limited warranty and liability — Information in this document is believed to be accurate and reliable. However, NXP Semiconductors does not give any representations or warranties, expressed or implied, as to the accuracy or completeness of such information and shall have no liability for the consequences of use of such information.

In no event shall NXP Semiconductors be liable for any indirect, incidental, punitive, special or consequential damages (including - without limitation - lost profits, lost savings, business interruption, costs related to the removal or replacement of any products or rework charges) whether or not such damages are based on tort (including negligence), warranty, breach of contract or any other legal theory.

Notwithstanding any damages that customer might incur for any reason whatsoever, NXP Semiconductors' aggregate and cumulative liability towards customer for the products described herein shall be limited in accordance with the *Terms and conditions of commercial sale* of NXP Semiconductors.

Right to make changes — NXP Semiconductors reserves the right to make changes to information published in this document, including without limitation specifications and product descriptions, at any time and without notice. This document supersedes and replaces all information supplied prior to the publication hereof.

Suitability for use — NXP Semiconductors products are not designed, authorized or warranted to be suitable for use in life support, life-critical or safety-critical systems or equipment, nor in applications where failure or

malfunction of an NXP Semiconductors product can reasonably be expected to result in personal injury, death or severe property or environmental damage. NXP Semiconductors accepts no liability for inclusion and/or use of NXP Semiconductors products in such equipment or applications and therefore such inclusion and/or use is at the customer's own risk.

Applications — Applications that are described herein for any of these products are for illustrative purposes only. NXP Semiconductors makes no representation or warranty that such applications will be suitable for the specified use without further testing or modification.

Customers are responsible for the design and operation of their applications and products using NXP Semiconductors products, and NXP Semiconductors accepts no liability for any assistance with applications or customer product design. It is customer's sole responsibility to determine whether the NXP Semiconductors product is suitable and fit for the customer's applications and products planned, as well as for the planned application and use of customer's third party customer(s). Customers should provide appropriate design and operating safeguards to minimize the risks associated with their applications and products.

NXP Semiconductors does not accept any liability related to any default, damage, costs or problem which is based on any weakness or default in the customer's applications or products, or the application or use by customer's third party customer(s). Customer is responsible for doing all necessary testing for the customer's applications and products using NXP Semiconductors products in order to avoid a default of the applications and the products or of the application or use by customer's third party customer(s). NXP does not accept any liability in this respect.

Limiting values — Stress above one or more limiting values (as defined in the Absolute Maximum Ratings System of IEC 60134) will cause permanent damage to the device. Limiting values are stress ratings only and (proper) operation of the device at these or any other conditions above those given in the Recommended operating conditions section (if present) or the Characteristics sections of this document is not warranted. Constant or repeated exposure to limiting values will permanently and irreversibly affect the quality and reliability of the device.

Terms and conditions of commercial sale — NXP Semiconductors products are sold subject to the general terms and conditions of commercial sale, as published at http://www.nxp.com/profile/terms, unless otherwise agreed in a valid written individual agreement. In case an individual agreement is concluded only the terms and conditions of the respective agreement shall apply. NXP Semiconductors hereby expressly objects to applying the customer's general terms and conditions with regard to the purchase of NXP Semiconductors products by customer.

No offer to sell or license — Nothing in this document may be interpreted or construed as an offer to sell products that is open for acceptance or the grant, conveyance or implication of any license under any copyrights, patents or other industrial or intellectual property rights.

Export control — This document as well as the item(s) described herein may be subject to export control regulations. Export might require a prior authorization from competent authorities.

12 of 14

Triple 3-input NAND gate

Non-automotive qualified products — Unless this data sheet expressly states that this specific NXP Semiconductors product is automotive qualified, the product is not suitable for automotive use. It is neither qualified nor tested in accordance with automotive testing or application requirements. NXP Semiconductors accepts no liability for inclusion and/or use of non-automotive qualified products in automotive equipment or applications.

In the event that customer uses the product for design-in and use in automotive applications to automotive specifications and standards, customer (a) shall use the product without NXP Semiconductors' warranty of the product for such automotive applications, use and specifications, and (b) whenever customer uses the product for automotive applications beyond

16. Contact information

NXP Semiconductors' specifications such use shall be solely at customer's own risk, and (c) customer fully indemnifies NXP Semiconductors for any liability, damages or failed product claims resulting from customer design and use of the product for automotive applications beyond NXP Semiconductors' standard warranty and NXP Semiconductors' product specifications.

15.4 Trademarks

Notice: All referenced brands, product names, service names and trademarks are the property of their respective owners.

For more information, please visit: http://www.nxp.com

For sales office addresses, please send an email to: salesaddresses@nxp.com

17. Contents

1	General description 1
2	Features and benefits 1
3	Ordering information 1
4	Functional diagram 2
5	Pinning information 2
5.1	Pinning
5.2	Pin description 2
6	Functional description 3
7	Limiting values 3
8	Recommended operating conditions 4
9	Static characteristics 4
10	Dynamic characteristics 5
11	AC waveforms 6
12	Package outline 7
13	Abbreviations 11
14	Revision history 11
15	Legal information 12
15.1	Data sheet status 12
15.2	Definitions 12
15.3	Disclaimers
15.4	Trademarks 13
16	Contact information 13
17	Contents 14

Please be aware that important notices concerning this document and the product(s) described herein, have been included in section 'Legal information'.

© NXP B.V. 2011.

All rights reserved.

For more information, please visit: http://www.nxp.com For sales office addresses, please send an email to: salesaddresses@nxp.com

Date of release: 17 November 2011 Document identifier: 74LVC10A

X-ON Electronics

Largest Supplier of Electrical and Electronic Components

Click to view similar products for Logic Gates category:

Click to view products by NXP manufacturer:

Other Similar products are found below :

5962-8769901BCA 74HC85N NL17SG08P5T5G NL17SG32DFT2G NLU1G32AMUTCG NLV7SZ58DFT2G NLVHC1G08DFT1G NLVVHC1G14DTT1G NLX2G08DMUTCG NLX2G08MUTCG MC74HCT20ADR2G 091992B 091993X 093560G 634701C 634921A NL17SG32P5T5G NL17SG86DFT2G NLU1G32CMUTCG NLV14001UBDR2G NLVVHC1G132DTT1G NLVVHC1G86DTT1G NLX1G11AMUTCG NLX1G97MUTCG 746427X 74AUP1G17FW5-7 74LS38 74LVC1G08Z-7 74LVC32ADTR2G 74LVC1G125FW4-7 74LVC08ADTR2G MC74HCT20ADTR2G NLU1G08CMX1TCG NLV14093BDTR2G NLV17SZ00DFT2G NLV17SZ02DFT2G NLV17SZ126DFT2G NLV27WZ17DFT2G NLV74HC02ADR2G NLV74HC08ADR2G NLVVHC1GT32DFT1G 74HC32S14-13 74LS133 74LVC1G32Z-7 M38510/30402BDA 74LVC1G86Z-7 74LVC2G08RA3-7 M38510/06202BFA NLV74HC08ADTR2G NLV74HC14ADR2G